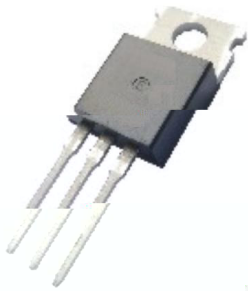
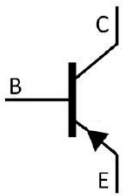


Rev. H Oct.-2018

TO-220 PNP Silicon PNP transistor in a TO-220 Plastic Package.

Large DC current($I_C=10A$),high f_T ($f_T \geq 2MHz$).

General purpose and switching applications.

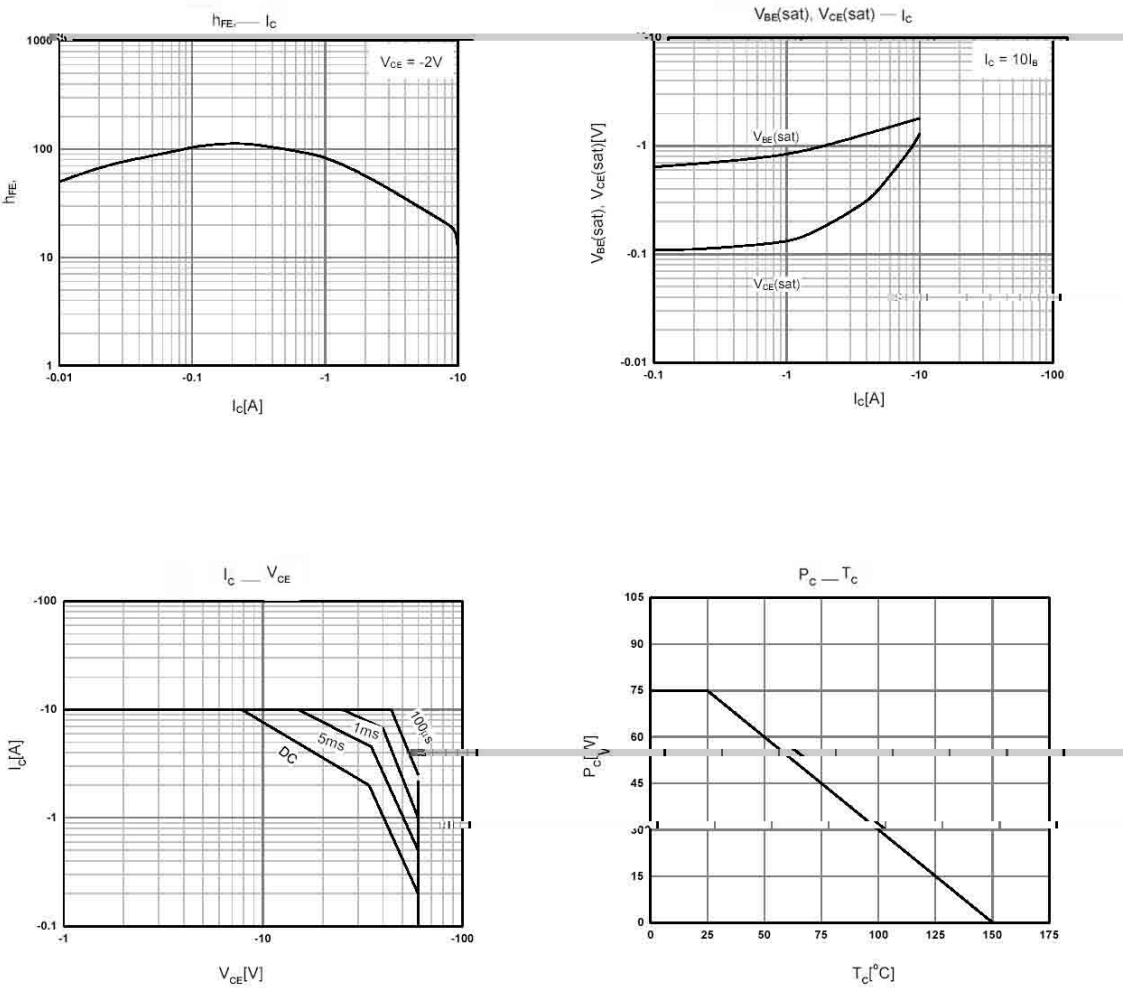


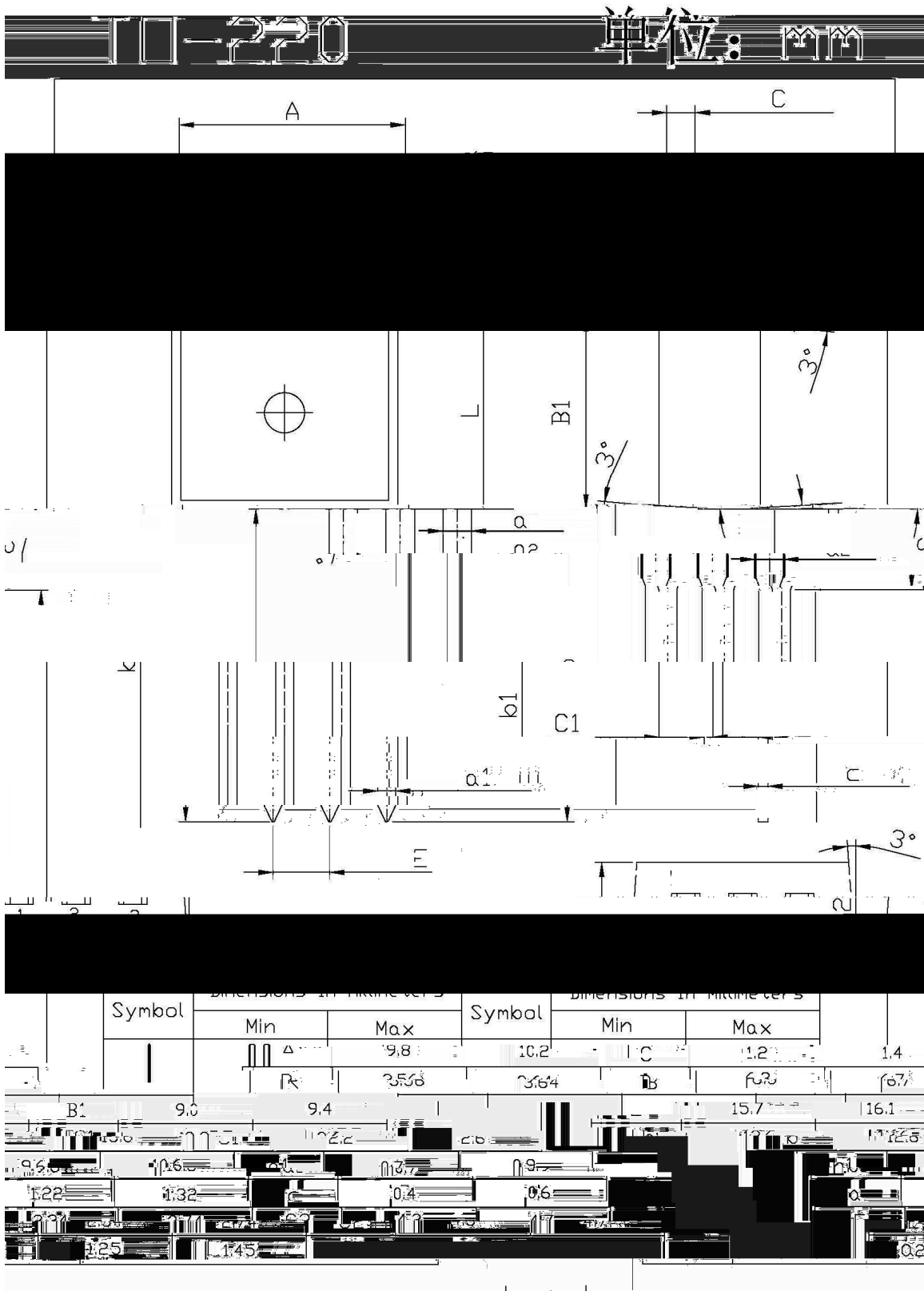
PIN1 Base PIN 2 Collector PIN 3 Emitter

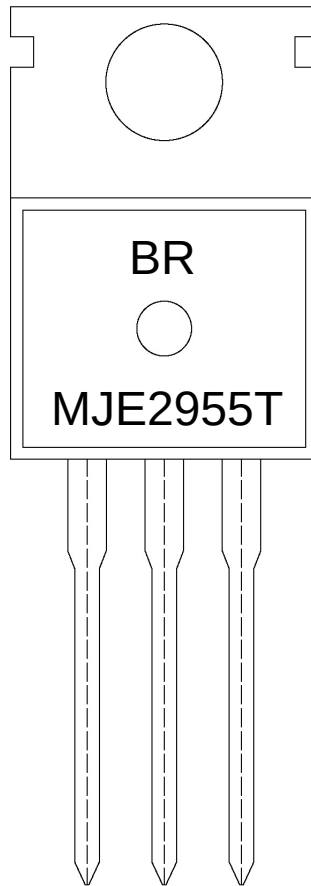
See Marking Instructions.

Parameter	Symbol	Rating	Unit
Collector to Base Voltage	V_{CBO}	-70	V
Collector to Emitter Voltage	V_{CEO}	-60	V
Emitter to Base Voltage	V_{EBO}	-5.0	V
Collector Current - Continuous	I_C	-10	A
Base Current - Continuous	I_B	-6.0	A
Collector Power Dissipation	P_C	2.0	W
	$P_C(T_c=25^{\circ}C)$	75	W
Junction Temperature	T_j	150	$^{\circ}C$
Storage Temperature Range	T_{stg}	-55 150	$^{\circ}C$

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector to Emitter Breakdown Voltage	V_{CEO}	$I_C=-200mA$ $I_B=0$	-60			V
Collector Cut-Off Current	I_{CEO}	$V_{CE}=-30V$ $I_B=0$			-700	A
Emitter Cut-Off Current	I_{EBO}	$V_{EB}=-5.0V$ $I_C=0$			-5.0	mA
Collector Cut-Off Current	I_{CEX}	$V_{BE(off)}=1.5V$ $V_{CE}=-70V$			-1.0	mA
DC Current Gain	$h_{FE(1)}$	$V_{CE}=-4.0V$ $I_C=-4.0A$	20		100	
	$h_{FE(2)}$	$V_{CE}=-4.0V$ $I_C=-10A$	5.0			
Collector to Emitter Saturation Voltage	$V_{CE(sat)(1)}$	$I_C=-4.0A$ $I_B=-0.4A$			-1.1	V
	$V_{CE(sat)(2)}$	$I_C=-10A$ $I_B=-3.3A$			-8.0	V
Base to Emitter On Voltage	$V_{BE(on)}$	$V_{CE}=-4.0V$ $I_C=-4.0A$			-1.8	V
Transition Frequency	f_T	$V_{CE}=-10V$ $I_C=-500mA$	2.0			MHz







BR

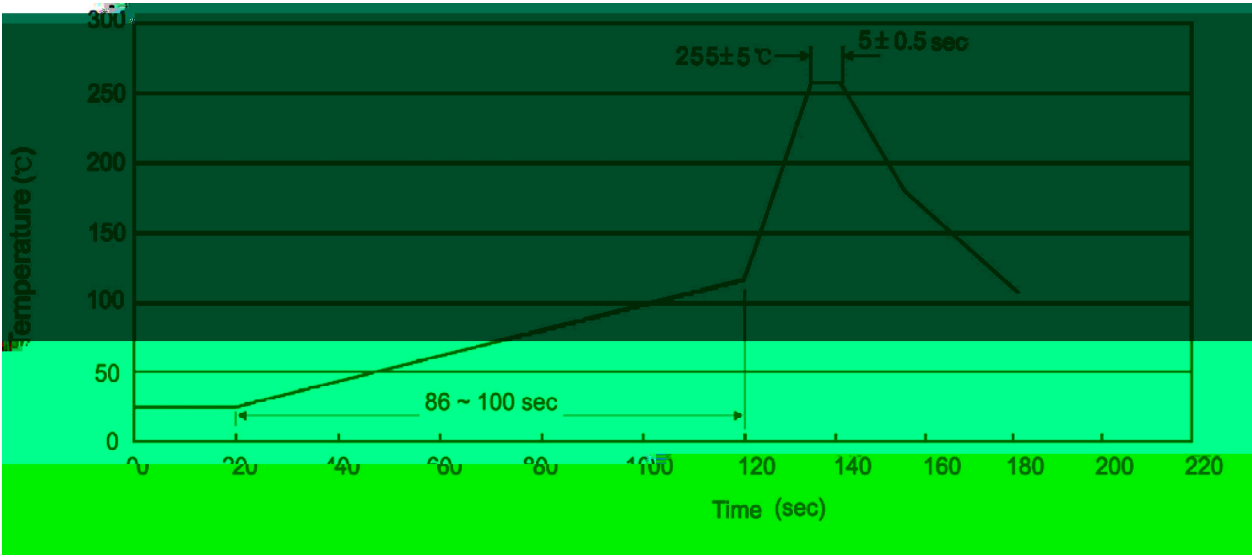
MJE2955T

Note:

BR: Company Code

MJE2955T: Product Type.

****: Lot No. Code, code change with Lot No.



Note:

- 1

25 150

60 90sec;
- 2

255±5

5±0.5sec;
- 3

2 10

/sec.
- 1.Preheating:25~150

, Time:60~90sec.
- 2.Peak Temp.:255±5

, Duration:5±0.5sec.
3. Cooling Speed: 2~10

/sec.

270±5

10±1 sec.

Temp.:270±5℃

Time:10±1 sec

/ BULK

Package Type	Units					Dimension (unit mm ³)		

/ TUBE

Package Type	Units					Dimension (unit mm ³)		